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IN THE CLAIMS

1. (Cancelled)
2. (New) A method for etching a substrate, comprising:
 - (a) etching the substrate in a first step, wherein the first step comprises:
supplying a first etch gas at a first rate to a first portion of the substrate through a first flow channel; and
supplying the first etch gas at a second rate to a second portion of the substrate through a second flow channel, wherein the first rate is different than the second rate; and
 - (b) etching the substrate in a second step, wherein the second step comprises:
supplying a second etch gas at a third rate to the first portion of the substrate through the first flow channel; and
supplying the second etch gas at a fourth rate to the second portion of the substrate through the second flow channel, wherein the third rate is different than the fourth rate.
3. (New) The method of claim 2, wherein the first gas is different than the second gas.
4. (New) The method of claim 2, wherein the first rate is greater than the second rate.
5. (New) The method of claim 2, wherein the first rate is less than the second rate.
6. (New) The method of claim 2, wherein the third rate is greater than the fourth rate.

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7. (New) The method of claim 2, wherein the third rate is less than the fourth rate.
8. (New) The method of claim 2, further comprising:
supplying the first gas to the first portion for a first period of time; and
supplying the first gas to the second portion for a second period of time
that is different than the first period of time.
9. (New) The method of claim 2, further comprising:
supplying the second gas to the first portion for a first period of time; and
supplying the second gas to the second portion for a second period of time
that is different than the first period of time.
10. (New) The method of claim 2, wherein the first portion is an inner portion
of the substrate and the second portion is an outer portion of the substrate.
11. (New) The method of claim 2, further comprising:
supplying the first gas to at least a third portion of the substrate.
12. (New) The method of claim 2, wherein the first step etches a first layer of
the substrate.
13. (New) The method of claim 12, wherein the second step etches the first
layer of the substrate.
14. (New) The method of claim 12, wherein the second step etches a second
layer of the substrate.
15. (New) The method of claim 2, wherein the first gas is supplied to the first
portion of the substrate through a first flow controller and to the second portion of
the substrate through a second flow controller.

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16. (New) The method of claim 15, wherein the second gas is supplied to the first portion of the substrate through the first flow controller and to the second portion of the substrate through the second flow controller.

17. (New) A method for etching a substrate, comprising:

controlling the supply of a first etch gas to a first portion of the substrate through a first flow channel and to a second portion of the substrate through a second flow channel to etch the substrate during a first etch step; and

controlling the supply of a second etch gas to the first portion of the substrate through the first flow channel and to the second portion of the substrate through the second flow channel during a second etch step.

18. (New) The method of claim 17, wherein the first gas is supplied to the first portion of the substrate through a first flow controller and to the second portion of the substrate through a second flow controller.

19. (New) The method of claim 18, wherein the second gas is supplied to the first portion of the substrate through the first flow controller and to the second portion of the substrate through the second flow controller.

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